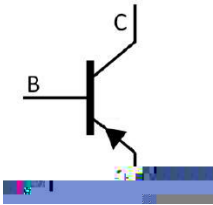


Silicon PNP transistor in a TO-252 Plastic Package.

Low $V_{CE(sat)}$, excellent DC current gain characteristics, complements the 2SD2118.

Medium power amplifier applications.



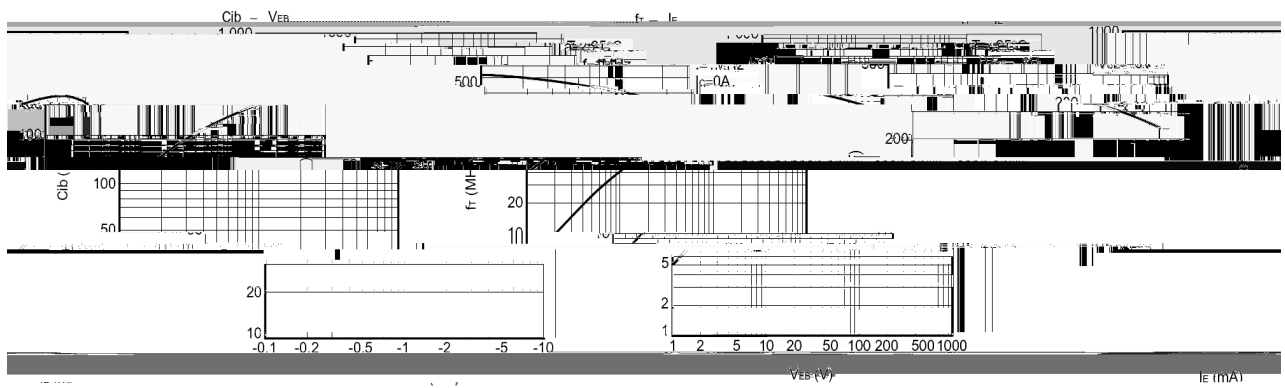
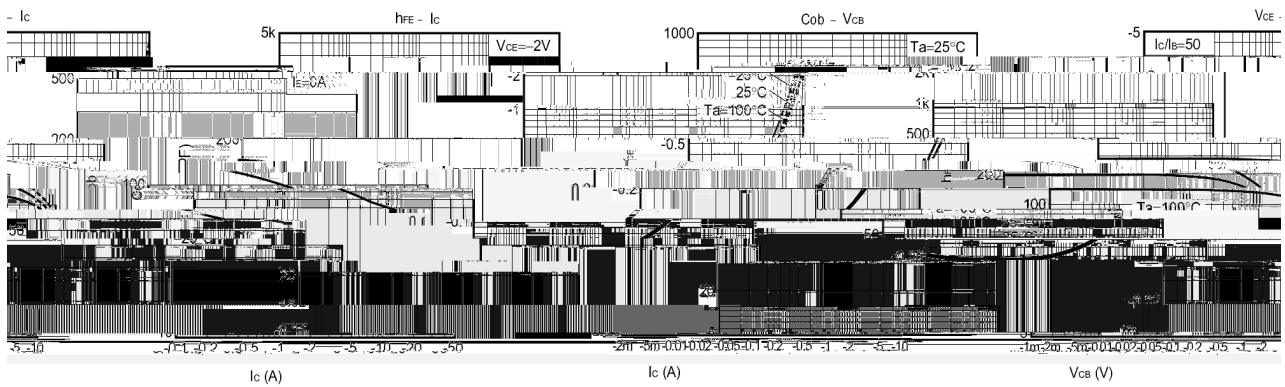
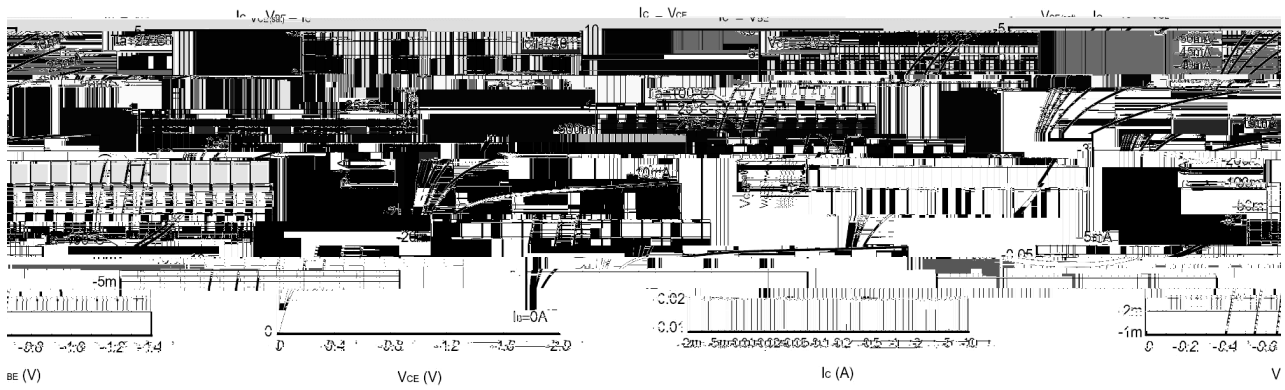
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

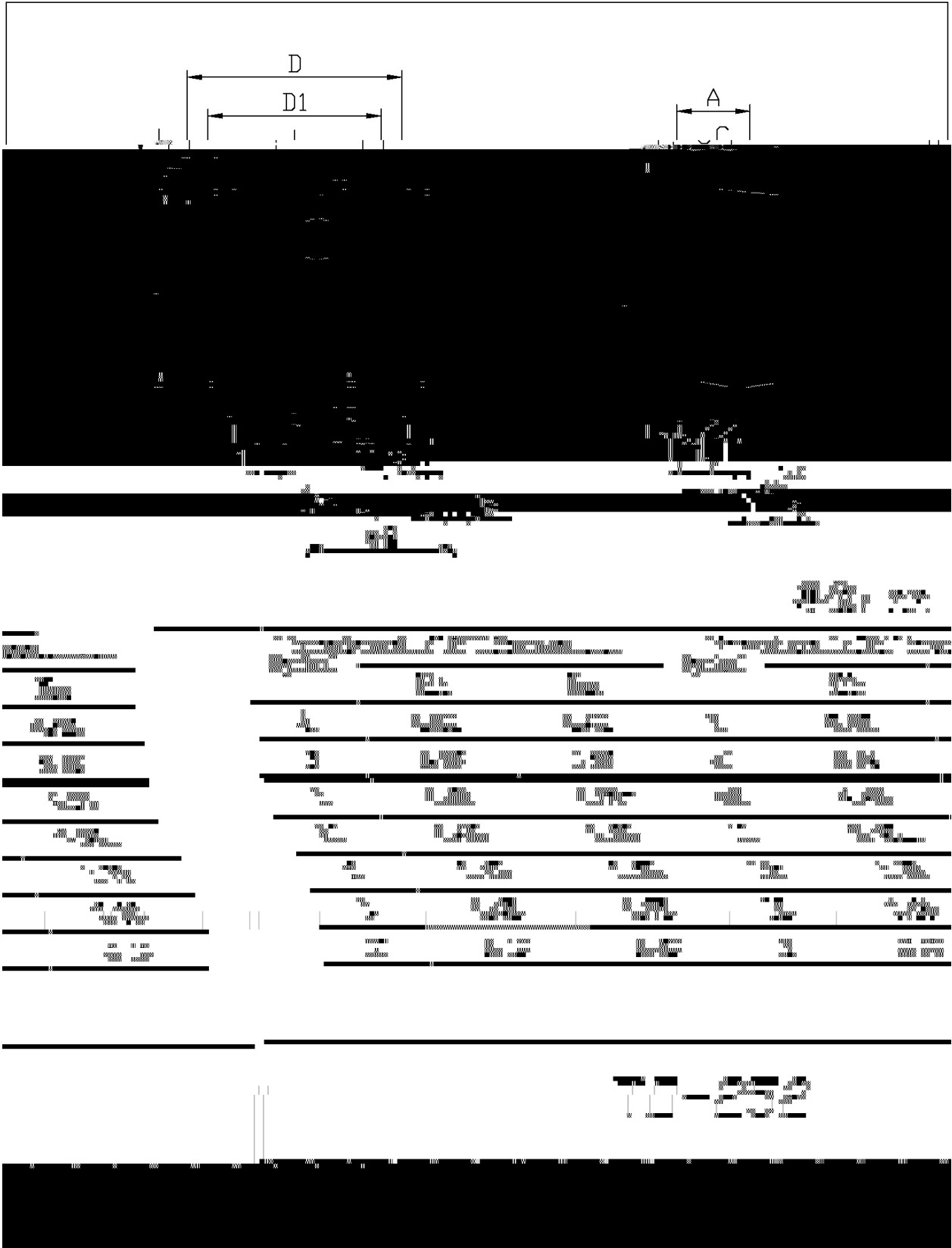
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390

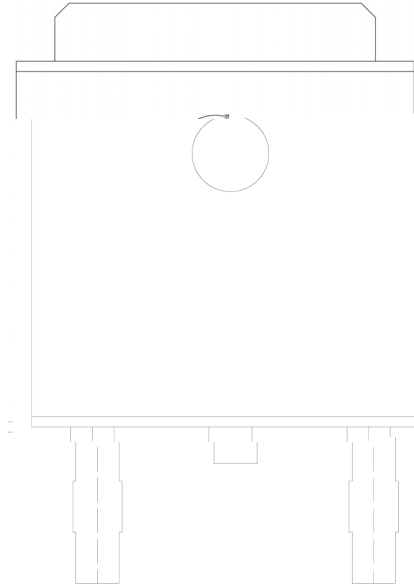
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-5	A
Peak Collector Current – Continuous	I_{CM}	-10	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation*	$*P_C(T_C=25 \text{ } ^\circ\text{C})$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*mounted On40×40×0.7mm ceramic board.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-50\mu\text{A}$ $I_E=0$	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0\text{mA}$ $I_B=0$	-20			V







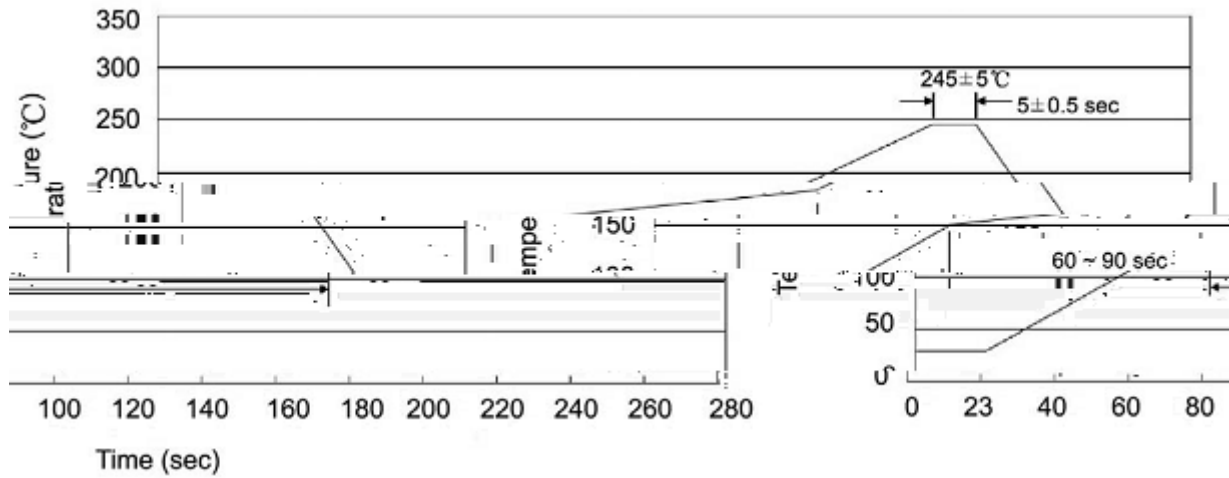
BR

h_{FE}

Note:

BR:

Company C (P:4.327372D0 Tc041e04b80556)Tj0941Tj/TTD(T

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

260 ± 5 10 ± 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	5	25,000	13	×16	